











SN74LVC2G06

SCES307J-AUGUST 2001-REVISED JULY 2015

SN74LVC2G06 Dual Inverter Buffer and Driver With Open-Drain Outputs

Features

- Available in the Texas Instruments Package
- Supports 5-V V_{CC} Operation
- Max t_{pd} of 3.4 ns at 3.3 V
- Low Power Consumption, 10-µA Max I_{CC}
- ±24-mA Output Drive at 3.3 V
- Typical V_{OLP} (Output Ground Bounce) $< 0.8 \text{ V at V}_{CC} = 3.3 \text{ V}, T_A = 25^{\circ}\text{C}$
- Typical V_{OHV} (Output V_{OH} Undershoot) >2 V at V_{CC} = 3.3 V, T_A = 25°C
- Inputs and Open-Drain Outputs Accept Voltages up to 5.5 V
- I_{off} Supports Live Insertion, Partial-Power-Down Mode and Back-Drive Protection
- Latch-Up Performance Exceeds 100 mA Per JESD 78, Class II
- Supports Down-Translation (5 V to 3.3 V and 3.3 V to 1.8 V)
- ESD Protection Exceeds JESD 22
 - 2000-V Human Body Model (A114-A)
 - 200-V Machine Model (A115-A)
 - 1000-V Charged-Device Model (C101)

2 Applications

- **AV Receivers**
- Blu-ray Players and Home Theaters
- **DVD** Recorders and Players
- Desktop or Notebook PCs
- Digital Radio or Internet Radio Players
- Digital Video Cameras (DVC)
- Embedded PC
- **GPS: Personal Navigation Devices**
- Mobile Internet Devices
- Network Projector Front-End
- Portable Media Players
- Pro Audio Mixers
- **Smoke Detectors**
- Solid-State Drive (SSD): Enterprise
- High-Definition (HDTV)

3 Description

This dual inverter buffer and driver is designed for 1.65-V to 5.5-V V_{CC} operation.

The output of the SN74LVC2G06 device is an opendrain which can be connected to other open-drain outputs to implement active-low, wired-OR, or activehigh wired-AND functions. The maximum sink current is 32 mA.

This device is fully specified for partial-power-down applications using I_{off} . The I_{off} circuitry disables the outputs, preventing damaging current backflow through the device when it is powered down.

NanoFree™ package technology is a major breakthrough in IC packaging concepts, using the die as the package.

Device Information(1)

ORDER NUMBER	PACKAGE	BODY SIZE (NOM)
SN74LVC2G06DBV	SOT-23 (6)	2.90 mm × 1.60 mm
SN74LVC2G06DCK	SC70 (6)	2.00 mm × 1.25 mm
SN74LVC2G06DRY	SON (6)	1.45 mm × 1.00 mm
SN74LVC2G06DSF	SON (6)	1.00 mm × 1.00 mm
SN74LVC2G06YZP	DSBGA (6)	1.41 mm × 0.91 mm

(1) For all available packages, see the orderable addendum at the end of the data sheet.

Logic Diagram

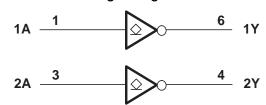




Table of Contents

Features 1		8.1 Overview	9
Applications 1		8.2 Functional Block Diagram	9
		8.3 Feature Description	9
-		8.4 Device Functional Modes	9
_	9	Application and Implementation	10
_		9.1 Application Information	10
•		9.2 Typical Application	10
· · · · · · · · · · · · · · · · · · ·	10	Power Supply Recommendations	11
•	11	Layout	11
		11.1 Layout Guidelines	11
		11.2 Layout Example	11
	12	Device and Documentation Support	12
· ·			
•		12.2 Trademarks	12
		12.3 Electrostatic Discharge Caution	12
,, , , , , , , , , , , , , , , , , , ,		12.4 Glossary	12
Detailed Description9	13		12
	Applications 1 Description 1 Revision History 2 Pin Configuration and Functions 3 Specifications 4 6.1 Absolute Maximum Ratings 4 6.2 ESD Ratings 4 6.3 Recommended Operating Conditions 5 6.4 Thermal Information 5 6.5 Electrical Characteristics 6 6.6 Switching Characteristics for -40°C to 85°C 6 6.7 Switching Characteristics for -40°C to 125°C 6 6.8 Operating Characteristics 6 6.9 Typical Characteristics 7 Parameter Measurement Information 8	Applications 1 Description 1 Revision History 2 Pin Configuration and Functions 3 Specifications 4 6.1 Absolute Maximum Ratings 4 6.2 ESD Ratings 4 6.3 Recommended Operating Conditions 5 6.4 Thermal Information 5 6.5 Electrical Characteristics 6 6.6 Switching Characteristics for -40°C to 85°C 6 6.7 Switching Characteristics for -40°C to 125°C 6 6.8 Operating Characteristics 6 6.9 Typical Characteristics 7 Parameter Measurement Information 8	Applications 1 8.2 Functional Block Diagram 8.3 Feature Description 8.4 Device Functional Modes 9 Application and Implementation 9.1 Application Information 9.2 Typical Application 9.2 Typical Appli

4 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

Changes from Revision I (December 2013) to Revision J

Page

Changes from Revision H (August 2012) to Revision I

Page

•	Updated document to new TI data sheet format.	. 1	
	Removed Ordering Information table.		
	Added ESD warning		
•	Updated operating temperature range.		

Changes from Revision G (January 2007) to Revision H

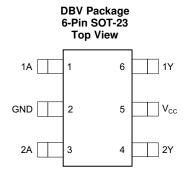
Page

Submit Documentation Feedback

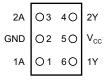
Copyright © 2001–2015, Texas Instruments Incorporated

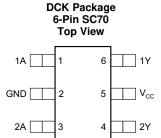


5 Pin Configuration and Functions

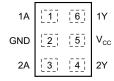




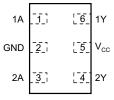








DSF Package 6-Pin SON Top View



Pin Functions

PIN		I/O	DESCRIPTION					
NAME	NO	1/0	DESCRIPTION					
GND	2	_	Ground					
1A	1	I	Input 1					
2A	3	1	Input 2					
1Y	6	1	Open-drain output 1					
2Y	4	0	Open-drain output 2					
V _{CC}	5	_	Power pin					



6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted) (1)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		-0.5	6.5	V
VI	Input voltage ⁽²⁾		-0.5	6.5	V
Vo	Voltage applied to any output in the high-impedance or power-off state (2)			6.5	V
V _O	Voltage applied to any output in the high or low state (2)(3)		-0.5	6.5	V
I _{IK}	Input clamp current	V _I < 0		-50	mA
I _{OK}	Output clamp current	V _O < 0		-50	mA
Io	Continuous output current			±50	mA
	Continuous current through V _{CC} or GND			±100	mA
T _{stg}	Storage Temperature		-65	150	°C

⁽¹⁾ Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions* is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

6.2 ESD Ratings

			VALUE	UNIT
		Human body model (HBM), per ANSI/ESDA/JEDEC JS-001 (1)	+2000	
V _(ESD)	Electrostatic discharge	Charged-device model (CDM), per JEDEC specification JESD22-C101 (2)	+1000	V

¹⁾ JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

⁽²⁾ The input negative-voltage and output voltage ratings may be exceeded if the input and output current ratings are observed.

⁽³⁾ The value of V_{CC} is provided in the *Recommended Operating Conditions* table.

⁽²⁾ JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.



6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)(1)

			MIN	NOM MAX	UNIT	
V	Connello contra con	Operating	1.65	5.5	.,	
v _{CC}	Supply voltage	Data retention only	1.5		V	
		V _{CC} = 1.65 V to 1.95 V	0.65 × V _{CC}			
\	Data retention on V_{CC} Supply voltage $V_{IH} = V_{IH} = V_{I$	V _{CC} = 2.3 V to 2.7 V	1.7		V	
V _{IH}		V _{CC} = 3 V to 3.6 V	2		V	
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	$0.7 \times V_{CC}$			
	Low-level input voltage	V _{CC} = 1.65 V to 1.95 V		$0.35 \times V_{CC}$		
V		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		0.7	V	
VIL		$V_{CC} = 3 \text{ V to } 3.6 \text{ V}$		0.8		
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$		$0.3 \times V_{CC}$		
V_{I}	Input voltage	*	0	5.5	V	
V_{O}	Output voltage		0	5.5	V	
		V _{CC} = 1.65 V		4		
		$V_{CC} = 2.3 \text{ V}$		8		
I_{OL}	Low-level output current	V 2.V		16	mA	
		VCC = 3 V		24		
		$V_{CC} = 4.5 \text{ V}$		32		
		$V_{CC} = 1.8 \text{ V} \pm 0.15 \text{ V}, 2.5 \text{ V} \pm 0.2 \text{ V}$		20		
$\Delta t/\Delta v$	Input transition rise or fall rate	$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$		10	-	
		$V_{CC} = 5 V \pm 0.5 V$		5		
T_A	Operating free-air temperature		-40	125	°C	

⁽¹⁾ All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, Implications of Slow or Floating CMOS Inputs, SCBA004.

6.4 Thermal Information

		SN74LVC2G06						
THERMAL METRIC ⁽¹⁾		DBV (SOT- 23)	DCK (SC70)	DRY (SON)	YPZ (DSBGA)	DSF (SON)	UNIT	
		6 PINS	6 PINS	6 PINS	6 PINS	6 PINS		
$R_{\theta JA}$	Junction-to-ambient thermal resistance	165	259	234	123	300	°C/W	

⁽¹⁾ For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report, SPRA953.



6.5 Electrical Characteristics

over recommended operating free-air temperature range (unless otherwise noted)

DADA	METER	TEST COMPLIANCE	V	-40°C to 85°C	–40°C to 125°C	LINUT
PARAMETER		TEST CONDITIONS	V _{CC}	MIN TYP ⁽¹⁾ MAX	MIN TYP ⁽¹⁾ MAX	UNIT
		I _{OL} = 100 μA	1.65 V to 5.5 V	0.1	0.1	
		I _{OL} = 4 mA	1.65 V	0.45	0.45	
N/		I _{OL} = 8 mA	2.3 V	0.3	0.3	V
V _{OL}	I _{OL} = 16 mA	3 V	0.4	0.4	v	
		I _{OL} = 24 mA	3 V	0.55	0.55	
		I _{OL} = 32 mA	4.5 V	0.55	0.55	
I _I	A inputs	V _I = 5.5 V or GND	0 to 5.5 V	±5	±5	μΑ
I _{off}		V_I or $V_O = 5.5 \text{ V}$	0	±10	±10	μΑ
I _{CC}		$V_I = 5.5 \text{ V or GND}, \qquad I_O = 0$	1.65 V to 5.5 V	10	10	μΑ
ΔI _{CC}		One input at V _{CC} – 0.6 V, Other inputs at V _{CC} or GND			500	μΑ
C _i		V _I = V _{CC} or GND	3.3 V	3.5	3.5	pF

⁽¹⁾ All typical values are at $V_{CC} = 3.3 \text{ V}$, $T_A = 25^{\circ}\text{C}$.

6.6 Switching Characteristics for -40°C to 85°C

over recommended operating free-air temperature range (unless otherwise noted) (see Figure 3)

PARAMETER	FROM (INPUT)			V _{CC} = 1.8 V ± 0.15 V		V _{CC} = 2.5 V ± 0.2 V		V _{CC} = 3.3 V ± 0.3 V		V _{CC} = 5 V ± 0.5 V	
	(INPOT)	(001701)	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t _{pd}	Α	Υ	1.8	7.2	1	3.9	1	3.4	1	2.9	ns

6.7 Switching Characteristics for -40°C to 125°C

over recommended operating free-air temperature range (unless otherwise noted) (see Figure 3)

PARAMETER	FROM	TO (OUTPUT)	V _{CC} = 1.8 V ± 0.15 V				V _{CC} = 3.3 V ± 0.3 V		V _{CC} = 5 V ± 0.5 V		UNIT
	(INPUT) ((OUTPUT)	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t _{pd}	Α	Y	1.8	8.2	1	4.4	1	3.9	1	3.4	ns

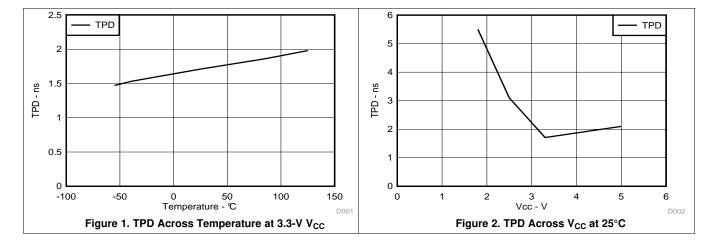
6.8 Operating Characteristics

 $T_{\Delta} = 25^{\circ}C$

	PARAMETER	TEST CONDITIONS	V _{CC} = 1.8 V	V _{CC} = 2.5 V	V _{CC} = 3.3 V	V _{CC} = 5 V	UNIT
	PARAMETER	TEST CONDITIONS	TYP	TYP	TYP	TYP	UNII
C_{pd}	Power dissipation capacitance	f = 10 MHz	2	2	3	4	pF



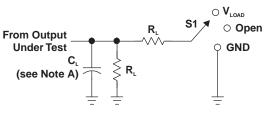
6.9 Typical Characteristics



Submit Documentation Feedback



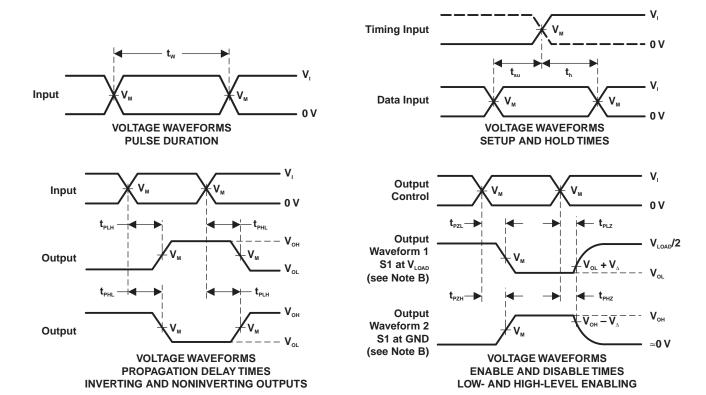
7 Parameter Measurement Information



TEST	S1
t _{PZL} (see Notes E and F)	V _{LOAD}
t _{PLZ} (see Notes E and G)	V _{LOAD}
t _{PHZ} /t _{PZH}	V _{LOAD}

Т	0	Δ	D	CI	R	CI	Ш	т

.,	INF	PUTS	.,	.,		В	.,
V _{cc}	CC V,		V _M	V _{LOAD}	C _∟	R _⊾	V _Δ
1.8 V ± 0.15 V	V _{cc}	≤2 ns	V _{cc} /2	2 × V _{cc}	30 pF	1 k Ω	0.15 V
2.5 V \pm 0.2 V	V _{cc}	≤ 2 ns	V _{cc} /2	2 × V _{cc}	30 pF	500 Ω	0.15 V
3.3 V \pm 0.3 V	3 V	≤2.5 ns	1.5 V	6 V	50 pF	500 Ω	0.3 V
5 V \pm 0.5 V	V _{cc}	≤2.5 ns	V _{cc} /2	2 × V _{cc}	50 pF	500 Ω	0.3 V



NOTES: A. C_L includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
- C. All input pulses are supplied by generators have the following characteristics: PRR \leq 10 MHz, Z_{o} = 50 Ω .
- D. The outputs are measured one at a time, with one transition per measurement.
- E. Because this device has open-drain outputs, t_{PLZ} and t_{PZL} are the same as t_{PD} .
- F. t_{PZL} is measured at V_{M} .
- G. t_{PLZ} is measured at $V_{OL} + V_{\Delta}$.
- H. All parameters and waveforms are not applicable to all devices.

Figure 3. Load Circuit and Voltage Waveforms (Open Drain)

Submit Documentation Feedback

Copyright © 2001–2015, Texas Instruments Incorporated



8 Detailed Description

8.1 Overview

The SN74LVC2G06 dual open-drain inverter device contains one open-drain inverter with a maximum sink current of 32 mA. This device is fully specified for partial-power-down applications using I_{off}. The I_{off} circuitry disables the outputs, preventing damaging current backflow through the device when it is powered down.

8.2 Functional Block Diagram



8.3 Feature Description

The wide operating voltage range of 1.65 V to 5.5 V allows the SN74LVC2G06 to be used in systems with many different voltage rails. In addition, the voltage tolerance on the output allows the device to be used for inverting up-translation or down-translation. The I_{OFF} feature safely allows voltage on the inputs and outputs when there's no V_{CC} is present.

8.4 Device Functional Modes

Table 1 lists the functional modes of the SN74LVC2G06.

Table 1. Function Table

INPUT A	OUTPUT Y
L	Hi-Z
Н	L



9 Application and Implementation

NOTE

Information in the following applications sections is not part of the TI component specification and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

9.1 Application Information

The SN74LVC2G06 is a dual high-drive CMOS device that implements a high-output drive buffer, such as an LED application. This device can sink 32 mA of current at 4.5 V making it ideal for high-drive applications and high-speed applications up to 100 MHz. The inputs are 5.5-V tolerant and let it to translate up or down to V_{CC} . The following *Typical Application* shows a simple LED driver application for a single channel of the device.

9.2 Typical Application

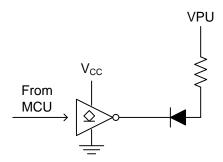


Figure 4. Typical Application Diagram

9.2.1 Design Requirements

This device uses CMOS technology and has balanced output drive. Avoid bus contention because it can drive currents that exceed maximum limits. The high drive also creates fast edges into light loads. Consider routing and load conditions to prevent ringing.

9.2.2 Detailed Design Procedure

- 1. Recommended Input Conditions
 - Rise time and fall time specs. See (Δt/ΔV) in the Recommended Operating Conditions table.
 - Specified high and low levels. See (V_{IH} and V_{IL}) in the Recommended Operating Conditions table.
 - Inputs are overvoltage tolerant allowing them to go as high as (V_I max) in the Recommended Operating
 Conditions table at any valid V_{CC}.

2. Recommend Output Conditions

- Load currents should not exceed (I_O max) per output and should not exceed (Continuous current through V_{CC} or GND) total current for the part. These limits are located in *Absolute Maximum Ratings* table.
- Do not pull outputs above 5.5 V.

Submit Documentation Feedback

Copyright © 2001–2015, Texas Instruments Incorporated



Typical Application (continued)

9.2.3 Application Curve

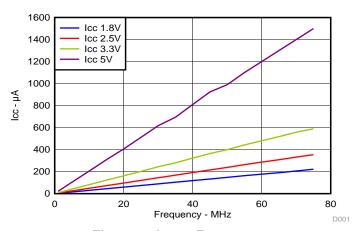


Figure 5. I_{CC} vs Frequency

10 Power Supply Recommendations

The power supply can be any voltage between the min and max supply voltage rating located in the Recommended Operating Conditions table.

Each V_{CC} pin must have a good bypass capacitor in order to prevent power disturbance. For devices with a single supply, a 0.1-μF capacitor is recommended and if there are multiple V_{CC} pins then a 0.01-μF or 0.022-μF capacitor is recommended for each power pin. It is ok to parallel multiple bypass caps to reject different frequencies of noise. 0.1-µF and 1-µF capacitors are commonly used in parallel. The bypass capacitor should be installed as close to the power pin as possible for best results.

Layout 11

11.1 Layout Guidelines

When using multiple bit logic devices, inputs must never float. In many cases, functions or parts of functions of digital logic devices are unused. Examples include when only two inputs of a triple input and gate are used or when only three of the four buffer gates are used. Avoid leaving input pins unconnected because the undefined voltages at the outside connections result in undefined operational states. Observe the following rules under all circumstances. Connect all unused inputs of digital logic devices to a high or low bias to prevent them from floating. Based on the function of the device, apply the logic level to any unused input. Based on convenience, tie unused inputs to the GND or the V_{CC} .

11.2 Layout Example

Copyright © 2001-2015, Texas Instruments Incorporated



Figure 6. Layout Recommendation



12 Device and Documentation Support

12.1 Community Resources

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

TI E2E™ Online Community TI's Engineer-to-Engineer (E2E) Community. Created to foster collaboration among engineers. At e2e.ti.com, you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.

Design Support *TI's Design Support* Quickly find helpful E2E forums along with design support tools and contact information for technical support.

12.2 Trademarks

NanoFree, E2E are trademarks of Texas Instruments. All other trademarks are the property of their respective owners.

12.3 Electrostatic Discharge Caution



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

12.4 Glossary

SLYZ022 — TI Glossary.

This glossary lists and explains terms, acronyms, and definitions.

13 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.





10-Dec-2020

PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
							(6)				
SN74LVC2G06DBVR	ACTIVE	SOT-23	DBV	6	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	(C065, C06R)	Samples
SN74LVC2G06DBVRE4	ACTIVE	SOT-23	DBV	6	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	(C065, C06R)	Samples
SN74LVC2G06DCKR	ACTIVE	SC70	DCK	6	3000	RoHS & Green	NIPDAU SN	Level-1-260C-UNLIM	-40 to 125	(CT5, CTJ, CTR)	Samples
SN74LVC2G06DCKRE4	ACTIVE	SC70	DCK	6	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	CT5	Samples
SN74LVC2G06DCKRG4	ACTIVE	SC70	DCK	6	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	CT5	Samples
SN74LVC2G06DRYR	ACTIVE	SON	DRY	6	5000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	СТ	Samples
SN74LVC2G06DSFR	ACTIVE	SON	DSF	6	5000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	СТ	Samples
SN74LVC2G06YZPR	ACTIVE	DSBGA	YZP	6	3000	RoHS & Green	SNAGCU	Level-1-260C-UNLIM	-40 to 85	(CT7, CTN)	Samples

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

⁽³⁾ MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

⁽⁴⁾ There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

⁽⁵⁾ Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.



PACKAGE OPTION ADDENDUM

10-Dec-2020

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

OTHER QUALIFIED VERSIONS OF SN74LVC2G06:

Automotive: SN74LVC2G06-Q1

Enhanced Product: SN74LVC2G06-EP

NOTE: Qualified Version Definitions:

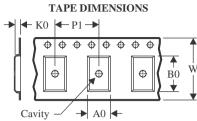
- Automotive Q100 devices qualified for high-reliability automotive applications targeting zero defects
- Enhanced Product Supports Defense, Aerospace and Medical Applications



www.ti.com 4-May-2023

TAPE AND REEL INFORMATION





A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE

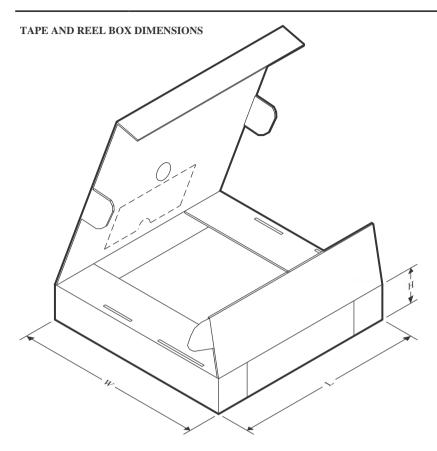


*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74LVC2G06DBVR	SOT-23	DBV	6	3000	178.0	9.2	3.3	3.23	1.55	4.0	8.0	Q3
SN74LVC2G06DBVR	SOT-23	DBV	6	3000	180.0	8.4	3.23	3.17	1.37	4.0	8.0	Q3
SN74LVC2G06DCKR	SC70	DCK	6	3000	178.0	9.0	2.4	2.5	1.2	4.0	8.0	Q3
SN74LVC2G06DCKR	SC70	DCK	6	3000	178.0	9.2	2.4	2.4	1.22	4.0	8.0	Q3
SN74LVC2G06DCKR	SC70	DCK	6	3000	180.0	8.4	2.41	2.41	1.2	4.0	8.0	Q3
SN74LVC2G06DCKRG4	SC70	DCK	6	3000	178.0	9.2	2.4	2.4	1.22	4.0	8.0	Q3
SN74LVC2G06DRYR	SON	DRY	6	5000	180.0	9.5	1.15	1.6	0.75	4.0	8.0	Q1
SN74LVC2G06DSFR	SON	DSF	6	5000	180.0	9.5	1.16	1.16	0.5	4.0	8.0	Q2
SN74LVC2G06YZPR	DSBGA	YZP	6	3000	178.0	9.2	1.02	1.52	0.63	4.0	8.0	Q1



www.ti.com 4-May-2023

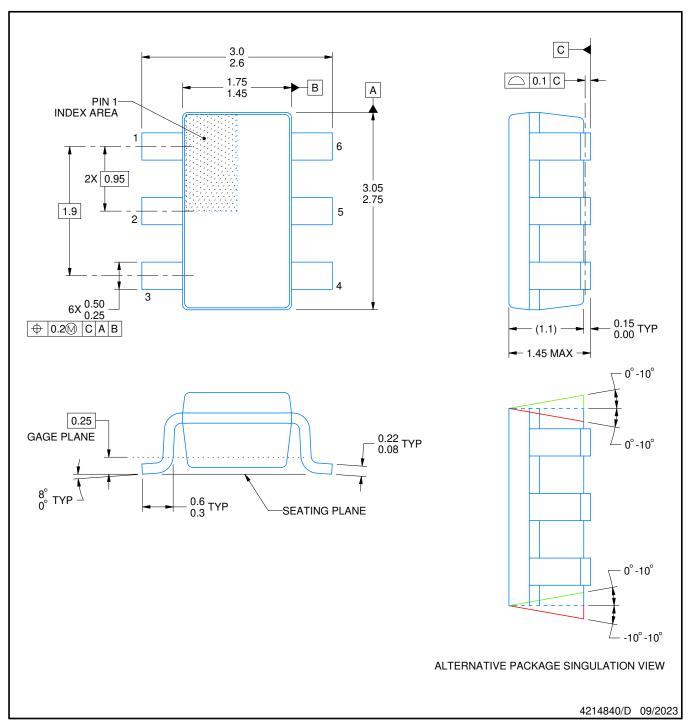


*All dimensions are nominal

7 til dilliciololio die Hollindi							
Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN74LVC2G06DBVR	SOT-23	DBV	6	3000	180.0	180.0	18.0
SN74LVC2G06DBVR	SOT-23	DBV	6	3000	202.0	201.0	28.0
SN74LVC2G06DCKR	SC70	DCK	6	3000	180.0	180.0	18.0
SN74LVC2G06DCKR	SC70	DCK	6	3000	180.0	180.0	18.0
SN74LVC2G06DCKR	SC70	DCK	6	3000	202.0	201.0	28.0
SN74LVC2G06DCKRG4	SC70	DCK	6	3000	180.0	180.0	18.0
SN74LVC2G06DRYR	SON	DRY	6	5000	184.0	184.0	19.0
SN74LVC2G06DSFR	SON	DSF	6	5000	184.0	184.0	19.0
SN74LVC2G06YZPR	DSBGA	YZP	6	3000	220.0	220.0	35.0



SMALL OUTLINE TRANSISTOR



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

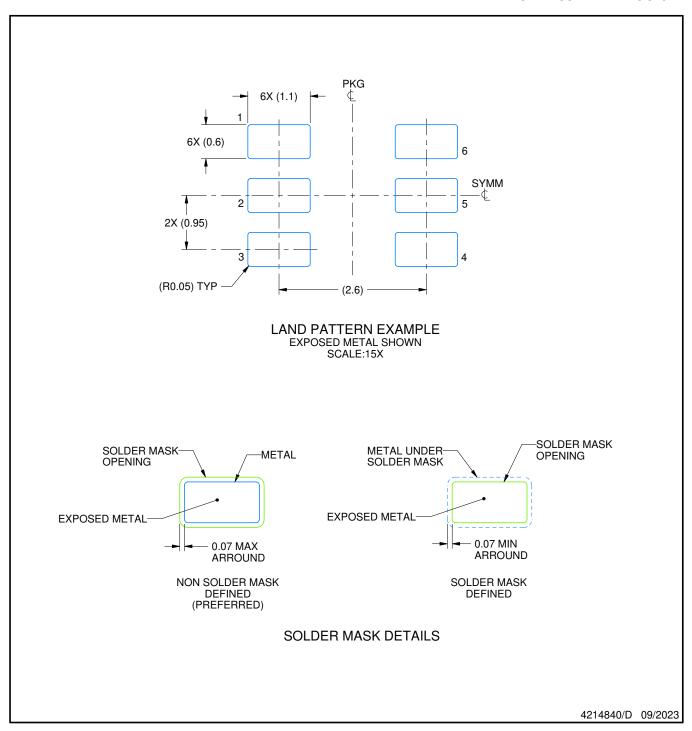
 2. This drawing is subject to change without notice.

 3. Body dimensions do not include mold flash or protrusion. Mold flash and protrusion shall not exceed 0.25 per side.

- 4. Leads 1,2,3 may be wider than leads 4,5,6 for package orientation. 5. Refernce JEDEC MO-178.



SMALL OUTLINE TRANSISTOR

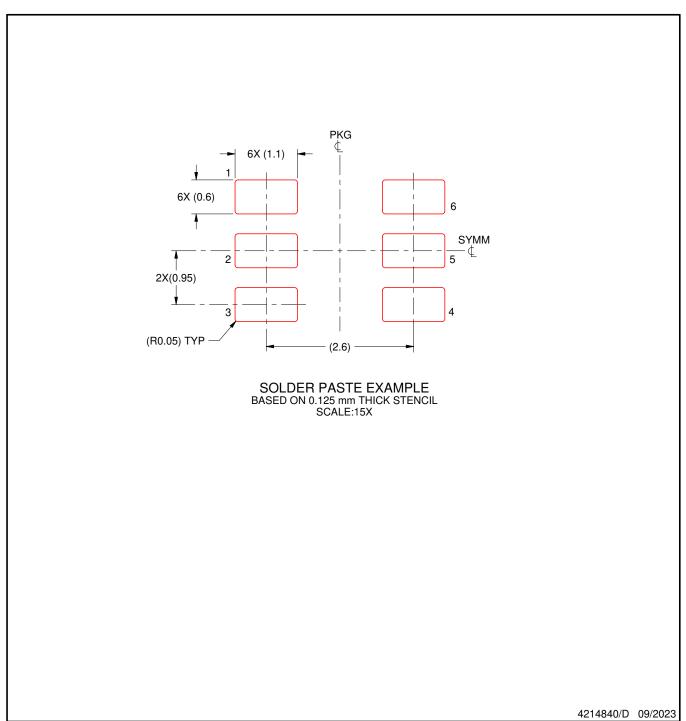


NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SMALL OUTLINE TRANSISTOR



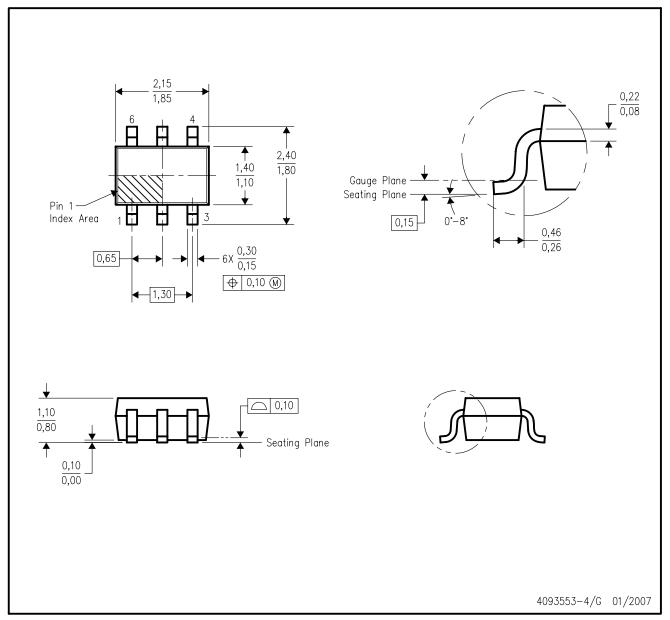
NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



DCK (R-PDSO-G6)

PLASTIC SMALL-OUTLINE PACKAGE



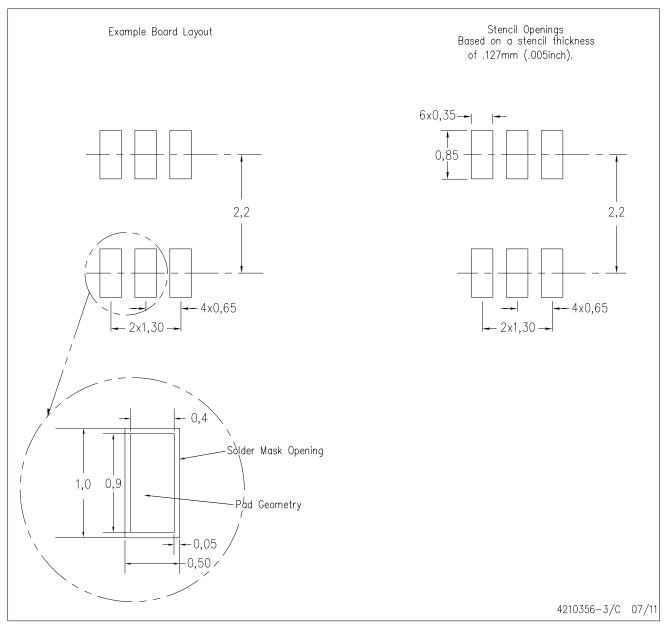
NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion. Mold flash and protrusion shall not exceed 0.15 per side.
- D. Falls within JEDEC MO-203 variation AB.



DCK (R-PDSO-G6)

PLASTIC SMALL OUTLINE



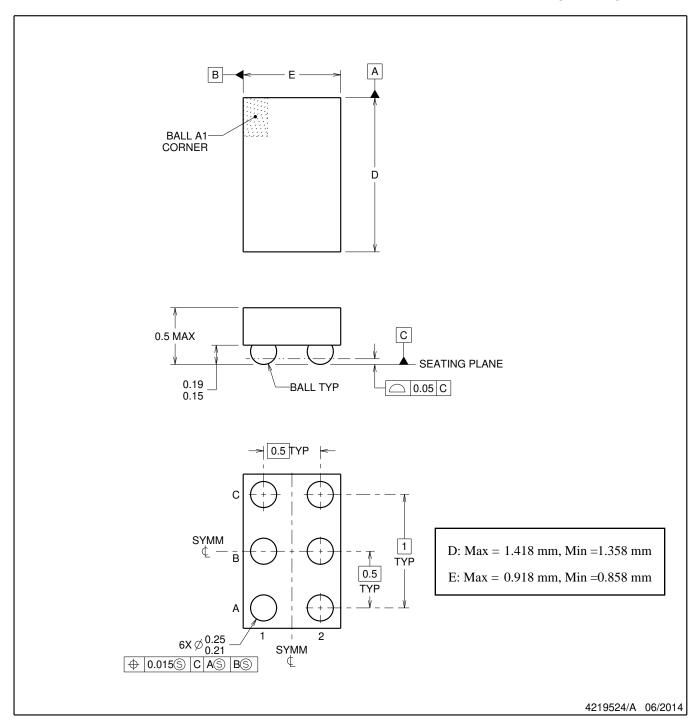
NOTES:

- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Customers should place a note on the circuit board fabrication drawing not to alter the center solder mask defined pad.
- D. Publication IPC-7351 is recommended for alternate designs.
- E. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Example stencil design based on a 50% volumetric metal load solder paste. Refer to IPC-7525 for other stencil recommendations.





DIE SIZE BALL GRID ARRAY



NOTES:

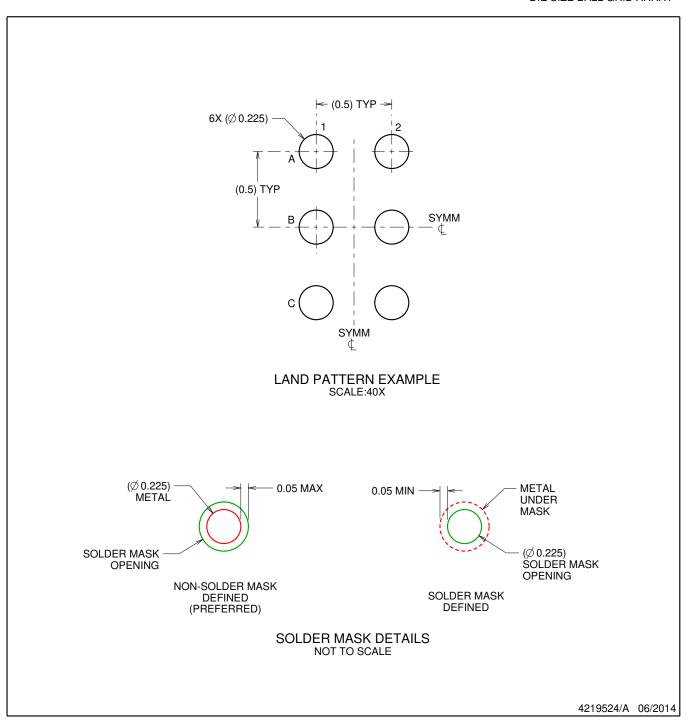
NanoFree Is a trademark of Texas Instruments.

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.
- 3. NanoFree[™] package configuration.



DIE SIZE BALL GRID ARRAY

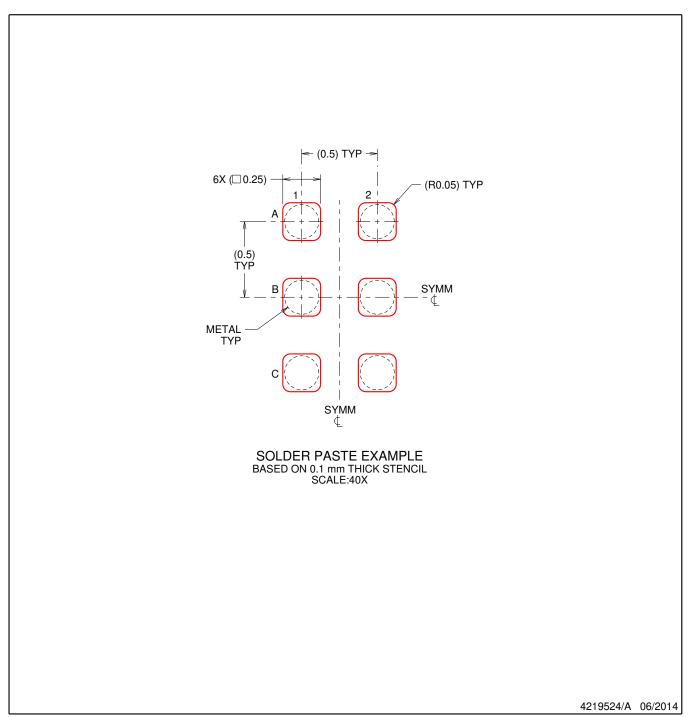


NOTES: (continued)

4. Final dimensions may vary due to manufacturing tolerance considerations and also routing constraints. For more information, see Texas Instruments literature number SBVA017 (www.ti.com/lit/sbva017).



DIE SIZE BALL GRID ARRAY



NOTES: (continued)

5. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release.



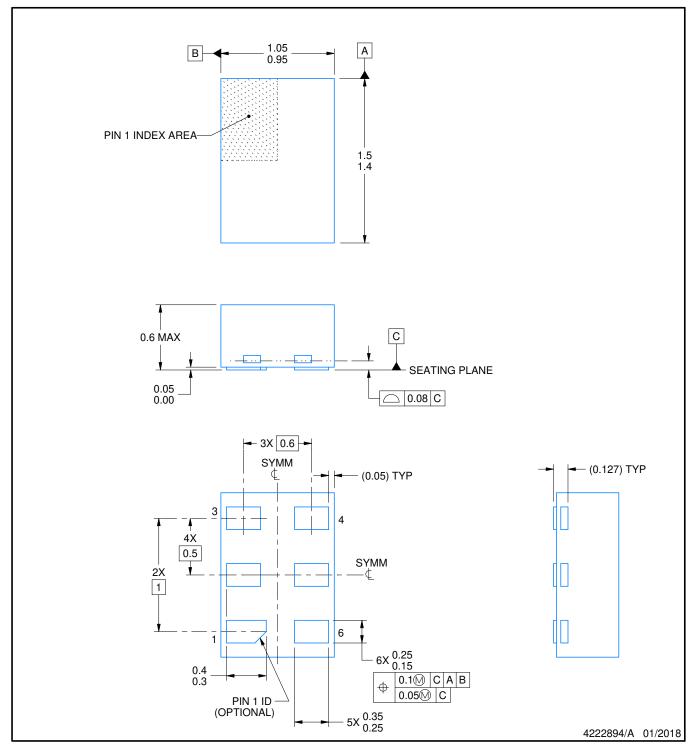


Images above are just a representation of the package family, actual package may vary. Refer to the product data sheet for package details.

4207181/G





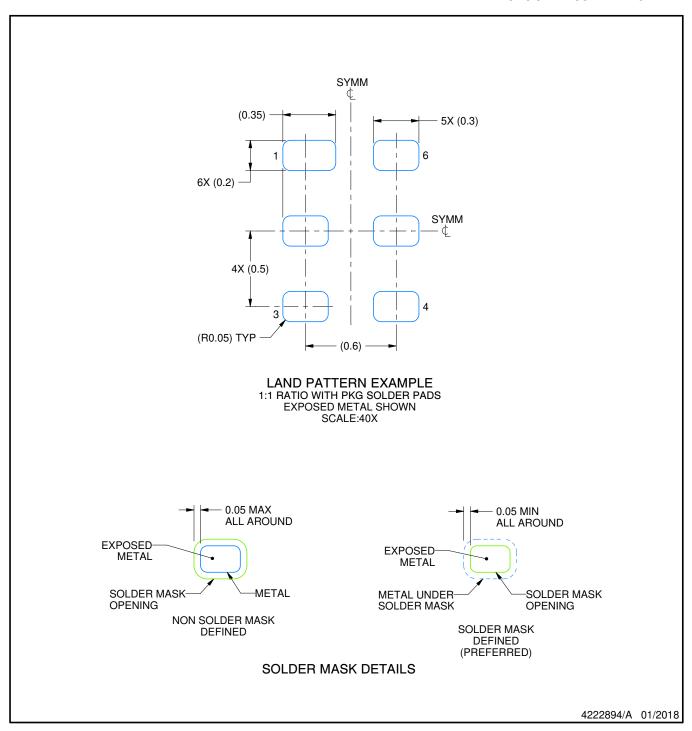


NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.

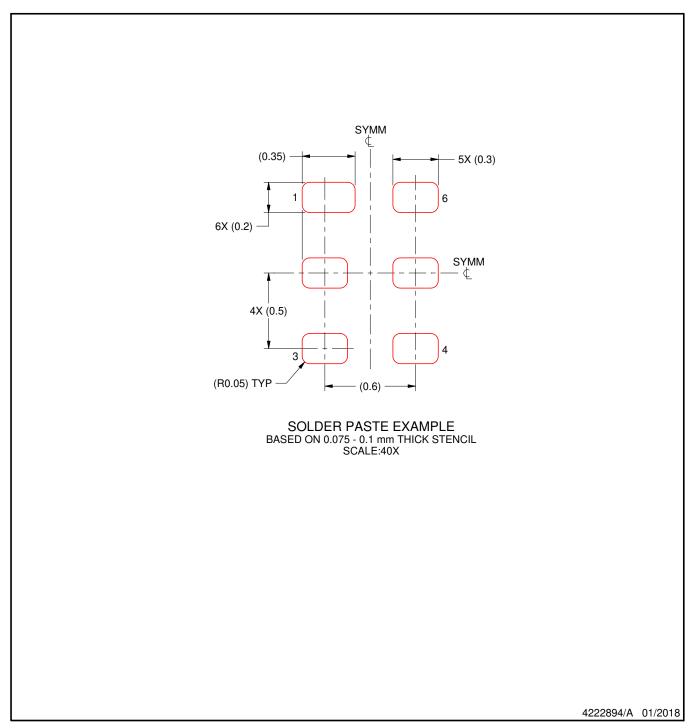




NOTES: (continued)

3. For more information, see QFN/SON PCB application report in literature No. SLUA271 (www.ti.com/lit/slua271).



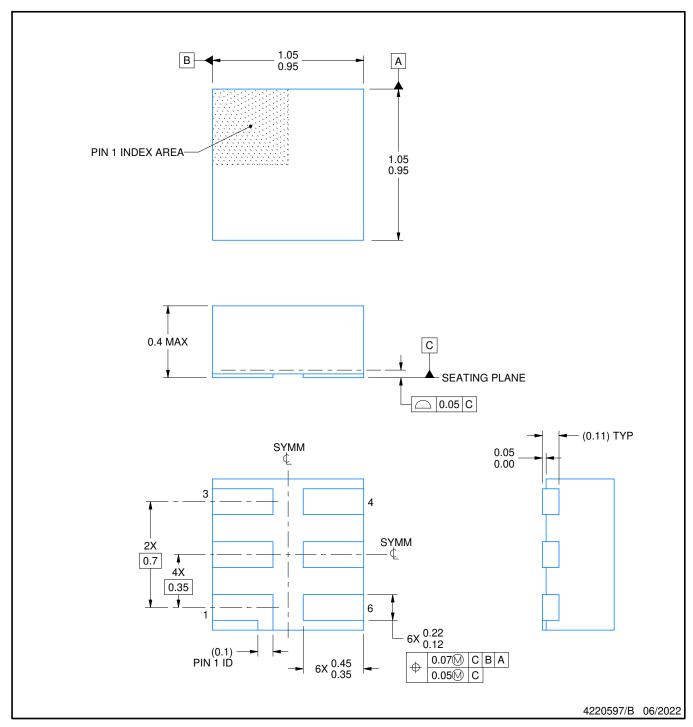


NOTES: (continued)

4. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.







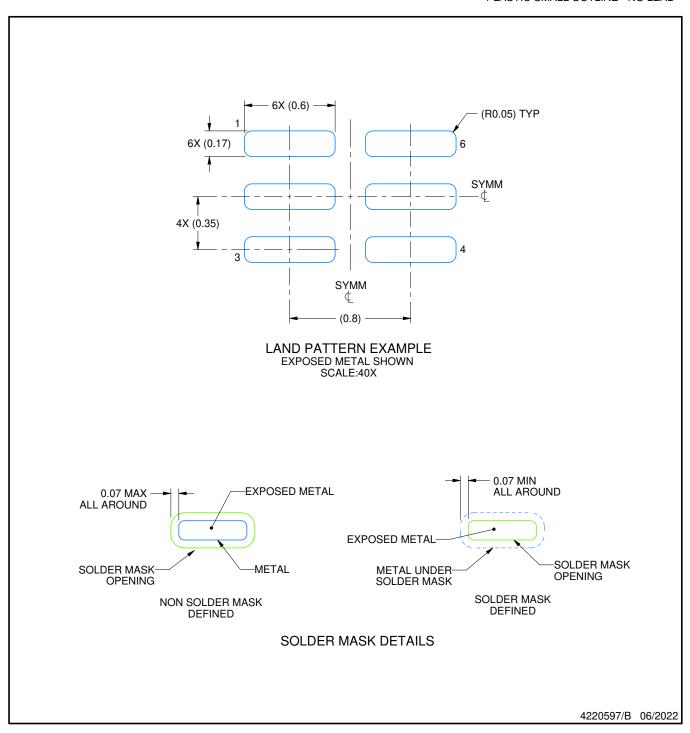
NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.

 3. Reference JEDEC registration MO-287, variation X2AAF.

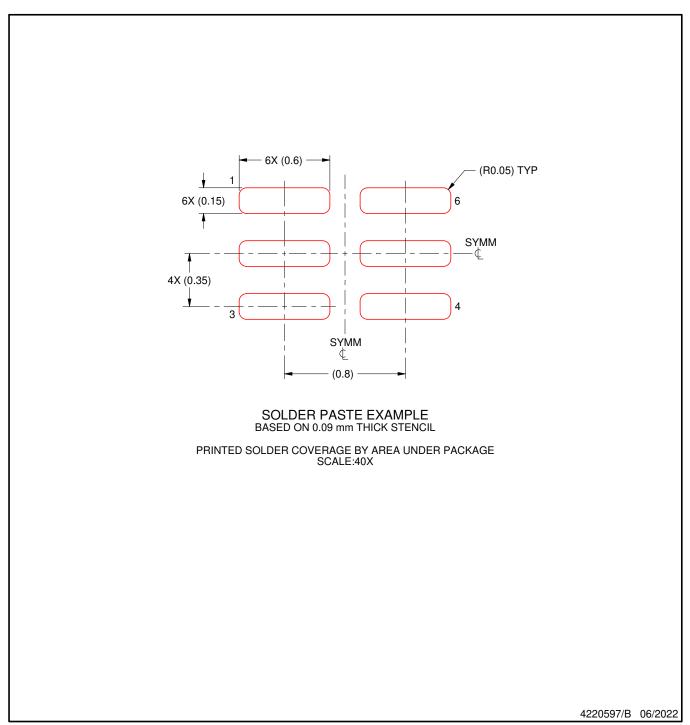




NOTES: (continued)

4. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).





4. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.



IMPORTANT NOTICE AND DISCLAIMER

TI PROVIDES TECHNICAL AND RELIABILITY DATA (INCLUDING DATA SHEETS), DESIGN RESOURCES (INCLUDING REFERENCE DESIGNS), APPLICATION OR OTHER DESIGN ADVICE, WEB TOOLS, SAFETY INFORMATION, AND OTHER RESOURCES "AS IS" AND WITH ALL FAULTS, AND DISCLAIMS ALL WARRANTIES, EXPRESS AND IMPLIED, INCLUDING WITHOUT LIMITATION ANY IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE OR NON-INFRINGEMENT OF THIRD PARTY INTELLECTUAL PROPERTY RIGHTS.

These resources are intended for skilled developers designing with TI products. You are solely responsible for (1) selecting the appropriate TI products for your application, (2) designing, validating and testing your application, and (3) ensuring your application meets applicable standards, and any other safety, security, regulatory or other requirements.

These resources are subject to change without notice. TI grants you permission to use these resources only for development of an application that uses the TI products described in the resource. Other reproduction and display of these resources is prohibited. No license is granted to any other TI intellectual property right or to any third party intellectual property right. TI disclaims responsibility for, and you will fully indemnify TI and its representatives against, any claims, damages, costs, losses, and liabilities arising out of your use of these resources.

TI's products are provided subject to TI's Terms of Sale or other applicable terms available either on ti.com or provided in conjunction with such TI products. TI's provision of these resources does not expand or otherwise alter TI's applicable warranties or warranty disclaimers for TI products.

TI objects to and rejects any additional or different terms you may have proposed.

Mailing Address: Texas Instruments, Post Office Box 655303, Dallas, Texas 75265 Copyright © 2023, Texas Instruments Incorporated